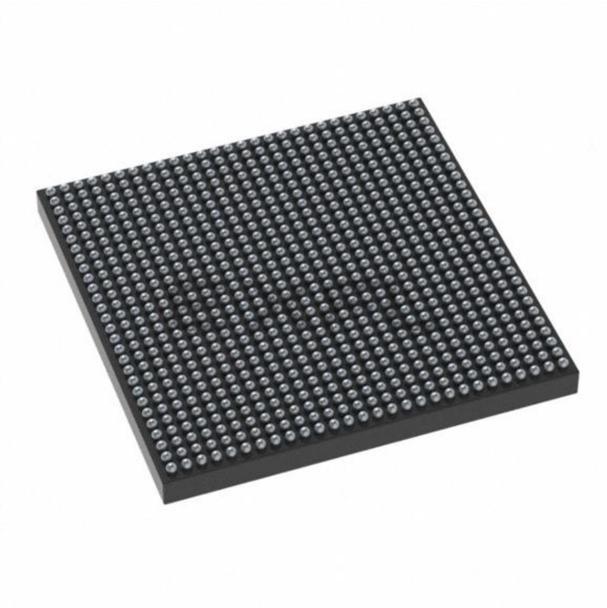

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Embedded - System On Chip (SoC): The Heart of Modern Embedded Systems

Embedded - System On Chip (SoC) refers to an integrated circuit that consolidates all the essential components of a computer system into a single chip. This includes a microprocessor, memory, and other peripherals, all packed into one compact and efficient package. SoCs are designed to provide a complete computing solution, optimizing both space and power consumption, making them ideal for a wide range of embedded applications.

What are Embedded - System On Chip (SoC)?

System On Chip (SoC) integrates multiple functions of a computer or electronic system onto a single chip. Unlike traditional multi-chip solutions, SoCs combine a central

Details	
Product Status	Active
Architecture	MCU, FPGA
Core Processor	Dual ARM® Cortex®-A53 MPCore™ with CoreSight™, Dual ARM®Cortex™-R5 with CoreSight™
Flash Size	-
RAM Size	256KB
Peripherals	DMA, WDT
Connectivity	CANbus, EBI/EMI, Ethernet, I²C, MMC/SD/SDIO, SPI, UART/USART, USB OTG
Speed	500MHz, 1.2GHz
Primary Attributes	Zynq®UltraScale+™ FPGA, 103K+ Logic Cells
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	784-BFBGA, FCBGA
Supplier Device Package	784-FCBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xczu2cg-l1sfvc784i

Table 2: **Recommended Operating Conditions[1][2]** ***(Cont'd)***

Symbol	Description	Min	Typ	Max	Units
PL System Monitor					
V_{CCADC}	PL System Monitor supply relative to GNDADC.	1.746	1.800	1.854	V
V_{REFP}	PL System Monitor externally supplied reference voltage relative to GNDADC.	1.200	1.250	1.300	V
Temperature					
T_j[13]	Junction temperature operating range for extended (E) temperature devices.[14]	0	–	100	°C
	Junction temperature operating range for industrial (I) temperature devices.	–40	–	100	°C
	Junction temperature operating range for eFUSE programming.	–40	–	125	°C

Notes:

1. All voltages are relative to GND.
2. For the design of the power distribution system consult *UltraScale Architecture PCB Design Guide* (UG583).
3. $V_{CC\_PSINTFP\_DDR}$ must be tied to $V_{CC\_PSINTFP}$.
4. Includes V_{CCO_PSDDR} of 1.2V, 1.35V, 1.5V at ±5% and 1.1V +0.07V/–0.04V depending upon the tolerances required by specific memory standards.
5. Applies to all PS I/O supply banks. Includes V_{CCO_PSIO} of 1.8V, 2.5V, and 3.3V at ±5%.
6. If the battery-backed RAM or RTC is not used, connect V_{CC_PSBATT} to GND or V_{CC_PSAUX}. The V_{CC_PSAUX} maximum of 1.89V is acceptable on an unused V_{CC_PSBATT}.
7. V_{CCINT_IO} must be connected to V_{CCBRAM}.
8. Includes V_{CCO} of 1.0V (HP I/O only), 1.2V, 1.35V, 1.5V, 1.8V, 2.5V (HD I/O only) at ±5%, and 3.3V (HD I/O only) at +3/–5%.
9. V_{CCAUX_IO} must be connected to V_{CCAUX}.
10. The lower absolute voltage specification always applies.
11. A total of 200 mA per bank should not be exceeded.
12. Each voltage listed requires filtering as described in *UltraScale Architecture GTH Transceiver User Guide* (UG576) or *UltraScale Architecture GTY Transceiver User Guide* (UG578).
13. Xilinx recommends measuring the Tj of a device using the system monitor as described in the *UltraScale Architecture System Monitor User Guide* (UG580). The SYSMON temperature measurement errors (that are described in Table 69 and Table 124) must be accounted for in your design. For example, when using the PL system monitor with an external reference of 1.25V, when SYSMON reports 97°C, there is a measurement error ±3°C. A reading of 97°C is considered the maximum adjusted Tj (100°C – 3°C = 97°C).
14. Devices labeled with the speed/temperature grade of -2LE normally operate under Extended (E) temperature grade specifications with a maximum junction temperature of 100°C. However, E temperature grade devices can operate for a limited time at a junction temperature of 110°C. Timing parameters adhere to the same speed file at 110°C as they do at 100°C, regardless of operating voltage (nominal voltage of 0.85V or a low-voltage of 0.72V). Operation at Tj = 110°C is limited to 1% of the device lifetime and can occur sequentially or at regular intervals as long as the total time does not exceed 1% of the device lifetime.

Available Speed Grades and Operating Voltages

Table 3 describes the speed grades per device and the V_{CCINT} operating supply voltages for the full-power, low-power, and DDR domains. For more information on selecting devices and speed grades, see the *UltraScale Architecture and Product Overview* (DS890).

Table 3: **Available Speed Grades and Operating Voltages**

Speed Grade	V_{CCINT}	$V_{CC\_PSINTLP}$	$V_{CC\_PSINTFP}$	$V_{CC\_PSINTFP\_DDR}$	Units
-3E	0.90	0.90	0.90	0.90	V
-2E	0.85	0.85	0.85	0.85	V
-2I	0.85	0.85	0.85	0.85	V
-2LE	0.85	0.85	0.85	0.85	V
-1E	0.85	0.85	0.85	0.85	V
-1I	0.85	0.85	0.85	0.85	V
-1LI	0.85	0.85	0.85	0.85	V
-2LE	0.72	0.85	0.85	0.85	V
-1LI	0.72	0.85	0.85	0.85	V

DC Characteristics Over Recommended Operating Conditions

Table 4: **DC Characteristics Over Recommended Operating Conditions**

Symbol	Description	Min	Typ(1)	Max	Units
V_{DRINT}	Data retention V_{CCINT} voltage (below which configuration data might be lost).	0.68	–	–	V
V_{DRAUX}	Data retention V_{CCAUX} voltage (below which configuration data might be lost).	1.5	–	–	V
I_{REF}	V_{REF} leakage current per pin.	–	–	15	µA
I_L	Input or output leakage current per pin (sample-tested).(2)	–	–	15	µA
C_{IN}(3)	Die input capacitance at the pad (HP I/O).	–	–	3.1	pF
	Die input capacitance at the pad (HD I/O).	–	–	4.75	pF
I_{RPU}	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 3.3V.	75	–	190	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 2.5V.	50	–	169	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 1.8V.	60	–	120	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 1.5V.	30	–	120	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 1.2V.	10	–	100	µA
I_{RPD}	Pad pull-down (when selected) at V_{IN} = 3.3V.	60	–	200	µA
	Pad pull-down (when selected) at V_{IN} = 1.8V.	29	–	120	µA
$I_{CCADCONPL}$	Analog supply current for the PL SYSMON circuits in the power-up state.	–	–	8	mA
$I_{CCADCONPS}$	Analog supply current for the PS SYSMON circuits in the power-up state.	–	–	10	mA
$I_{CCADCOFFPL}$	Analog supply current for the PL SYSMON circuits in the power-down state.	–	–	1.5	mA
$I_{CCADCOFFPS}$	Analog supply current for the PS SYSMON circuits in the power-down state.	–	–	1.8	mA

Table 4: **DC Characteristics Over Recommended Operating Conditions *(Cont'd)***

Symbol	Description	Min	Typ[1]	Max	Units
I_{CC_PSBATT}[4][5]	Battery supply current at V_{CC_PSBATT} = 1.50V, RTC enabled.	–	–	3650	nA
	Battery supply current at V_{CC_PSBATT} = 1.50V, RTC disabled.	–	–	650	nA
	Battery supply current at V_{CC_PSBATT} = 1.20V, RTC enabled.	–	–	3150	nA
	Battery supply current at V_{CC_PSBATT} = 1.20V, RTC disabled.	–	–	150	nA
I_{PSFS}[6]	PS V_{CC_PSAUX} additional supply current during eFUSE programming.	–	–	115	mA
Calibrated programmable on-die termination (DCI) in HP I/O banks[8] (measured per JEDEC specification)					
R[9]	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_40.	–10%[7]	40	+10%[7]	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_48.	–10%[7]	48	+10%[7]	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_60.	–10%[7]	60	+10%[7]	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_40.	–10%[7]	40	+10%[7]	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_48.	–10%[7]	48	+10%[7]	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_60.	–10%[7]	60	+10%[7]	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_120.	–10%[7]	120	+10%[7]	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_240.	–10%[7]	240	+10%[7]	Ω
Uncalibrated programmable on-die termination in HP I/Os banks (measured per JEDEC specification)					
R[9]	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_40.	–50%	40	+50%	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_48.	–50%	48	+50%	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_60.	–50%	60	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_40.	–50%	40	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_48.	–50%	48	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_60.	–50%	60	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_120.	–50%	120	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_240.	–50%	240	+50%	Ω
Uncalibrated programmable on-die termination in HD I/O banks (measured per JEDEC specification)					
R[9]	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_48.	–50%	48	+50%	Ω
Internal V_{REF}	50% V_{CCO}	V_{CCO} x 0.49	V_{CCO} x 0.50	V_{CCO} x 0.51	V
	70% V_{CCO}	V_{CCO} x 0.69	V_{CCO} x 0.70	V_{CCO} x 0.71	V

Table 9: **Typical Quiescent Supply Current[(1)(2)(3)(4)] *(Cont'd)***

Symbol	Description	Device	Speed Grade and V_{CCINT} Operating Voltages					Units
			0.90V	0.85V		0.72V		
			-3	-2	-1	-2	-1	
I_{CCAUX_IOQ}	Quiescent V_{CCAUX_IO} supply current.	XCZU2	N/A	26	26	26	26	mA
		XCZU3	N/A	26	26	26	26	mA
		XCZU4	32	32	32	32	32	mA
		XCZU5	32	32	32	32	32	mA
		XCZU6	33	33	33	33	33	mA
		XCZU7	56	56	56	56	56	mA
		XCZU9	33	33	33	33	33	mA
		XCZU11	56	56	56	56	56	mA
		XCZU15	33	33	33	33	33	mA
		XCZU17	74	74	74	74	74	mA
		XCZU19	74	74	74	74	74	mA
$I_{CCBRAMQ}$	Quiescent V_{CCBRAM} supply current.	XCZU2	N/A	6	6	6	6	mA
		XCZU3	N/A	6	6	6	6	mA
		XCZU4	9	9	9	9	9	mA
		XCZU5	9	9	9	9	9	mA
		XCZU6	25	24	24	24	24	mA
		XCZU7	16	15	15	15	15	mA
		XCZU9	25	24	24	24	24	mA
		XCZU11	23	22	22	22	22	mA
		XCZU15	29	28	28	28	28	mA
		XCZU17	37	35	35	35	35	mA
		XCZU19	37	35	35	35	35	mA

Notes:

1. Typical values are specified at nominal voltage, 85°C junction temperatures (T_j) with single-ended SelectIO™ resources.
2. Typical values are for blank configured devices with no output current loads, no active input pull-up resistors, all I/O pins are 3-state and floating.
3. Use the Xilinx Power Estimator (XPE) spreadsheet tool (download at www.xilinx.com/power) to estimate static power consumption for conditions or supplies other than those specified.
4. Typical values depend upon your configuration. To accurately estimate all PS supply currents, use the interactive XPE spreadsheet tool.

AC Switching Characteristics

All values represented in this data sheet are based on the speed specifications in the Vivado® Design Suite as outlined in Table 25.

Table 25: **Speed Specification Version By Device**

2017.1	Device
1.08	XCZU4CG, XCZU4EG, XCZU4EV, XCZU5CG, XCZU5EG, XCZU5EV, XCZU11EG
1.10	XCZU2CG, XCZU2EG, XCZU3CG, XCZU3EG, XCZU6CG, XCZU6EG, XCZU7CG, XCZU7EG, XCZU7EV, XCZU9CG, XCZU9EG, XCZU15EG, XCZU17EG, XCZU19EG

Switching characteristics are specified on a per-speed-grade basis and can be designated as Advance, Preliminary, or Production. Each designation is defined as follows:

Advance Product Specification

These specifications are based on simulations only and are typically available soon after device design specifications are frozen. Although speed grades with this designation are considered relatively stable and conservative, some under-reporting might still occur.

Preliminary Product Specification

These specifications are based on complete ES (engineering sample) silicon characterization. Devices and speed grades with this designation are intended to give a better indication of the expected performance of production silicon. The probability of under-reporting delays is greatly reduced as compared to Advance data.

Product Specification

These specifications are released once enough production silicon of a particular device family member has been characterized to provide full correlation between specifications and devices over numerous production lots. There is no under-reporting of delays, and customers receive formal notification of any subsequent changes. Typically, the slowest speed grades transition to production before faster speed grades.

Testing of AC Switching Characteristics

Internal timing parameters are derived from measuring internal test patterns. All AC switching characteristics are representative of worst-case supply voltage and junction temperature conditions.

For more specific, more precise, and worst-case guaranteed data, use the values reported by the static timing analyzer and back-annotate to the simulation net list. Unless otherwise noted, values apply to all Zynq UltraScale+ MPSoC.

Table 26: **Speed Grade Designations by Device *(Cont'd)***

Device	Speed Grade, Temperature Ranges, and V_{CCINT} Operating Voltages		
	Advance	Preliminary	Production
XCZU5EG	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU5EV	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU6CG	-2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V) -1LI (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.72V)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCZU6EG	-3E (V_{CCINT} = 0.90V) -2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V) -1LI (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.72V)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCZU7CG	-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU7EG	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU7EV	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU9CG	-2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V) -1LI (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.72V)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCZU9EG	-3E (V_{CCINT} = 0.90V) -2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V) -1LI (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.72V)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)

Table 26: **Speed Grade Designations by Device *(Cont'd)***

Device	Speed Grade, Temperature Ranges, and V_{CCINT} Operating Voltages		
	Advance	Preliminary	Production
XCZU11EG	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU15EG	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU17EG	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU19EG	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		

Notes:

1. The lowest power -1L and -2L devices, where V_{CCINT} = 0.72V, are listed in the Vivado Design Suite as -1LV and -2LV respectively.

Table 31: **PS NAND NV-DDR Synchronous Performance**

Memory Standard	Mode	Speed Grade			Units
		-3	-2	-1	
		Max	Max	Max	
NV-DDR[1]	5	200	200	200	Mb/s
	4	166.6	166.6	166.6	Mb/s
	3	133.3	133.3	133.3	Mb/s
	2	100	100	100	Mb/s
	1	66.6	66.6	66.6	Mb/s
	0	40	40	40	Mb/s

Notes:

1. The PS NAND memory controller interface for NV-DDR switching characteristics meets the requirements of the ONFI 3.1 specification.

Table 32: **PS NAND SDR Asynchronous Performance**

Memory Standard	Mode	Speed Grade			Units
		-3	-2	-1	
		Max	Max	Max	
SDR[1][2]	5	50	50	50	Mb/s
	4	40	40	40	Mb/s
	3	33.3	33.3	33.3	Mb/s
	2	28.5	28.5	28.5	Mb/s
	1	20	20	20	Mb/s
	0	10	10	10	Mb/s

Notes:

1. The PS NAND memory controller interface for SDR switching characteristics meets the requirements of the ONFI 3.1 specification.
2. The NAND controller reference clock frequency maximum is 83 MHz.

Table 33: **PS-PL Interface Performance**

Symbol	Description	Min	Max	Units
$F_{EMIOGEMCLK}$	EMIO gigabit Ethernet controller maximum frequency.	–	125	MHz
$F_{EMIOSDCLK}$	EMIO SD controller maximum frequency.	–	25	MHz
$F_{EMIOSPICLK}$	EMIO SPI controller maximum frequency.	–	25	MHz
$F_{EMIOTRACECLK}$	EMIO trace controller maximum frequency.	–	125	MHz
$F_{FCIDMACLK}$	Flow control interface DMA maximum frequency.	–	333	MHz
F_{AXICLK}	Maximum AXI interface performance.	–	333	MHz
$F_{DPLIVEVIDEO}$	DisplayPort controller live video interface maximum frequency.	–	300	MHz

Table 37: **PS Reset Assertion Timing Requirements**

Symbol	Description	Min	Typ	Max	Units
T_{PSPOR}	Required PS_POR_B assertion time.(1)	10	–	–	µs
T_{PSRST}	Required PS_SRST_B assertion time.	3	–	–	PS_REF_CLK Clock Cycles

Notes:

1. PS_POR_B must be asserted Low at power-up and continue to be asserted for a duration of T_{PSPOR} after all the PS supply voltages reach minimum levels. PS_POR_B must be asserted Low for the duration of T_{POR} when the PS and PL power-up at the same time and the application uses both the PS and PL after power-up.

Table 38: **PS Clocks Switching Characteristics**

Symbol	Description	Speed Grade			Units
		-3	-2	-1	
$F_{TOPSW\_MAINMAX}$	TOPSW_MAIN maximum frequency.	600	533	533	MHz
$F_{TOPSW\_LSBUSMAX}$	TOPSW_LSBUS maximum frequency.	100	100	100	MHz
$F_{GDMAMAX}$	FPD-DMA maximum frequency.	600	600	600	MHz
$F_{DPDMAMAX}$	DisplayPort DMA maximum frequency.	600	600	600	MHz
$F_{LPD\_SWITCH\_CTRLMAX}$	LPD_SWITCH_CTRL maximum frequency.	600	500	500	MHz
$F_{LPD\_LSBUS\_CTRLMAX}$	LPD_LSBUS_CTRL maximum frequency.	100	100	100	MHz
$F_{ADMAMAX}$	LPD-DMA maximum frequency.	600	500	500	MHz
$F_{APLL\_TO\_LPDMAX}$	APLL_TO_LPD maximum frequency.	533	533	533	MHz
$F_{DPLL\_TO\_LPDMAX}$	DPLL_TO_LPD maximum frequency.	533	533	533	MHz
$F_{VPLL\_TO\_LPDMAX}$	VPLL_TO_LPD maximum frequency.	533	533	533	MHz
$F_{IOPLL\_TO\_LPDMAX}$	IOPLL_TO_LPD maximum frequency.	533	533	533	MHz
$F_{RPLL\_TO\_FPDMAX}$	RPLL_TO_FPD maximum frequency.	533	533	533	MHz

Table 42: **Linear Quad-SPI Interface[(1)]**

Symbol	Description	Load Conditions[(2)]	Min	Max	Units
Quad-SPI device clock frequency operating at 100 MHz. Loopback enabled. LVCMOS 1.8V I/O standard.					
$T_{DCQSPICLK5}$	Quad-SPI clock duty cycle.	15 pF	45	55	%
		30 pF	45	55	%
$T_{QSPISSSCLK5}$	Slave select asserted to next clock edge.[(3)]	15 pF	5.0	–	ns
		30 pF	5.0	–	ns
$T_{QSPISCLKSS5}$	Clock edge to slave select deasserted.	15 pF	5.0	–	ns
		30 pF	5.0	–	ns
$T_{QSPICKO5}$	Clock to output delay, all outputs.	15 pF	3.2	7.4	ns
		30 pF	3.2	7.4	ns
$T_{QSPIDCK5}$	Setup time, all inputs.	15 pF	2.4	–	ns
		30 pF	2.4	–	ns
$T_{QSPICKD5}$	Hold time, all inputs.	15 pF	0.0	–	ns
		30 pF	0.0	–	ns
$F_{QSPIREFCLK5}$	Quad-SPI reference clock frequency.	15 pF	–	200	MHz
		30 pF	–	200	MHz
$F_{QSPICLK5}$	Quad-SPI device clock frequency.	15 pF	–	100	MHz
		30 pF	–	100	MHz

Notes:

1. The test conditions are configured for the linear Quad-SPI interface at 100 MHz with a 12 mA drive strength and fast slew rate.
2. 30 pF loads are for stacked modes.
3. $T_{QSPISSSCLK5}$ is only valid when two reference clock cycles are programmed between chip select and clock.

PS USB Interface

Table 43: **ULPI Interface[(1)]**

Symbol	Description	Min	Max	Units
$T_{ULPIDCK}$	Input setup to ULPI clock, all inputs.	4.5	–	ns
$T_{ULPICKD}$	Input hold to ULPI clock, all inputs.	0	–	ns
$T_{ULPICKO}$	ULPI clock to output valid, all outputs.	2.0	8.86	ns
$F_{ULPICLK}$	ULPI reference clock frequency.	–	60	MHz

Notes:

1. The test conditions are configured to the LVCMOS 3.3V I/O standard with a 12 mA drive strength, fast slew rate, and a 15 pF load.

PS-GTR Transceiver

Table 56: **PS-GTR Transceiver DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
DV_{PPIN}	Differential peak-to-peak input voltage (external AC coupled).		100	–	1200	mV
V_{IN}	Single-ended input voltage. Voltage measured at the pin referenced to GND.		75	–	$V_{PS\_MGTRAVCC}$	mV
V_{CMIN}	Common mode input voltage.		–	0	–	mV
D_{VPPOUT}	Differential peak-to-peak output voltage.(1)	Transmitter output swing is set to maximum value.	800	–	–	mV
$V_{CMOUTAC}$	Common mode output voltage: AC coupled (equation based).		$V_{PS\_MGTRAVCC} - D_{VPPOUT}/2$			mV
R_{IN}	Differential input resistance.		–	100	–	Ω
R_{OUT}	Differential output resistance.		–	100	–	Ω
$R_{MGTRREF}$	Resistor value between calibration resistor pin to GND.		497.5	500	502.5	Ω
T_{OSKEW}	Transmitter output pair (TXP and TXN) intra-pair skew (All packages).		–	–	20	ps
C_{EXT}	Recommended external AC coupling capacitor.(2)		–	100	–	nF

Notes:

1. The output swing and pre-emphasis levels are programmable using the attributes discussed in the *Zynq UltraScale+ MPSoC Technical Reference Manual* (UG1085), and can result in values lower than reported in this table.
2. Other values can be used as appropriate to conform to specific protocols and standards.

Table 57: **PS-GTR Transceiver Clock DC Input Level Specification**

Symbol	DC Parameter	Min	Typ	Max	Units
V_{IDIFF}	Differential peak-to-peak input voltage.	250	–	2000	mV
R_{IN}	Differential input resistance.	–	100	–	Ω
C_{EXT}	Required external AC coupling capacitor.	–	10	–	nF

Table 58: **PS-GTR Transceiver Performance**

Symbol	Description	Speed Grade			Units
		-3	-2	-1	
F_{GTRMAX}	PS-GTR maximum line rate.	6.0	6.0	6.0	Gb/s
F_{GTRMIN}	PS-GTR minimum line rate.	1.25	1.25	1.25	Gb/s

Table 59: **PS-GTR Transceiver PLL/Lock Time Adaptation**

Symbol	Description	Min	Typ	Max	Units
T_{LOCK}	Initial PLL lock.	–	–	0.11	ms
T_{DLOCK}	Clock recovery phase acquisition and adaptation time.	–	–	24×10^6	UI

Table 76: **IOB High Performance (HP) Switching Characteristics *(Cont'd)***

I/O Standards	$T_{INBUF\_DELAY\_PAD\_I}$					$T_{OUTBUF\_DELAY\_O\_PAD}$					$T_{OUTBUF\_DELAY\_TD\_PAD}$					Units
	0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		
	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	
DIFF_SSTL12_F	0.394	0.394	0.402	0.394	0.402	0.412	0.412	0.430	0.412	0.430	0.538	0.538	0.566	0.538	0.566	ns
DIFF_SSTL12_M	0.394	0.394	0.402	0.394	0.402	0.553	0.553	0.584	0.553	0.584	0.641	0.641	0.676	0.641	0.676	ns
DIFF_SSTL12_S	0.394	0.394	0.402	0.394	0.402	0.758	0.758	0.808	0.758	0.808	0.823	0.823	0.879	0.823	0.879	ns
DIFF_SSTL135_DCI_F	0.371	0.371	0.402	0.371	0.402	0.411	0.411	0.428	0.411	0.428	0.537	0.537	0.565	0.537	0.565	ns
DIFF_SSTL135_DCI_M	0.371	0.371	0.402	0.371	0.402	0.551	0.551	0.582	0.551	0.582	0.645	0.645	0.685	0.645	0.685	ns
DIFF_SSTL135_DCI_S	0.371	0.371	0.402	0.371	0.402	0.746	0.746	0.799	0.746	0.799	0.829	0.829	0.893	0.829	0.893	ns
DIFF_SSTL135_F	0.375	0.375	0.402	0.375	0.402	0.408	0.408	0.428	0.408	0.428	0.528	0.528	0.561	0.528	0.561	ns
DIFF_SSTL135_M	0.375	0.375	0.402	0.375	0.402	0.555	0.555	0.585	0.555	0.585	0.641	0.641	0.679	0.641	0.679	ns
DIFF_SSTL135_S	0.375	0.375	0.402	0.375	0.402	0.772	0.772	0.823	0.772	0.823	0.827	0.827	0.878	0.827	0.878	ns
DIFF_SSTL15_DCI_F	0.397	0.397	0.417	0.397	0.417	0.412	0.412	0.429	0.412	0.429	0.531	0.531	0.563	0.531	0.563	ns
DIFF_SSTL15_DCI_M	0.397	0.397	0.417	0.397	0.417	0.553	0.553	0.583	0.553	0.583	0.645	0.645	0.685	0.645	0.685	ns
DIFF_SSTL15_DCI_S	0.397	0.397	0.417	0.397	0.417	0.768	0.768	0.822	0.768	0.822	0.847	0.847	0.912	0.847	0.912	ns
DIFF_SSTL15_F	0.404	0.404	0.417	0.404	0.417	0.424	0.424	0.445	0.424	0.445	0.551	0.551	0.577	0.551	0.577	ns
DIFF_SSTL15_M	0.404	0.404	0.417	0.404	0.417	0.554	0.554	0.585	0.554	0.585	0.639	0.639	0.677	0.639	0.677	ns
DIFF_SSTL15_S	0.404	0.404	0.417	0.404	0.417	0.767	0.767	0.817	0.767	0.817	0.813	0.813	0.867	0.813	0.867	ns
DIFF_SSTL18_I_DCI_F	0.320	0.320	0.336	0.320	0.336	0.445	0.445	0.461	0.445	0.461	0.566	0.566	0.595	0.566	0.595	ns
DIFF_SSTL18_I_DCI_M	0.320	0.320	0.336	0.320	0.336	0.554	0.554	0.585	0.554	0.585	0.644	0.644	0.683	0.644	0.683	ns
DIFF_SSTL18_I_DCI_S	0.320	0.320	0.336	0.320	0.336	0.762	0.762	0.818	0.762	0.818	0.837	0.837	0.899	0.837	0.899	ns
DIFF_SSTL18_I_F	0.316	0.316	0.336	0.316	0.336	0.454	0.454	0.476	0.454	0.476	0.578	0.578	0.608	0.578	0.608	ns
DIFF_SSTL18_I_M	0.316	0.316	0.336	0.316	0.336	0.571	0.571	0.603	0.571	0.603	0.652	0.652	0.692	0.652	0.692	ns
DIFF_SSTL18_I_S	0.316	0.316	0.336	0.316	0.336	0.782	0.782	0.835	0.782	0.835	0.816	0.816	0.870	0.816	0.870	ns
HSLVDCI_15_F	0.393	0.393	0.415	0.393	0.415	0.425	0.425	0.443	0.425	0.443	0.548	0.548	0.579	0.548	0.579	ns
HSLVDCI_15_M	0.393	0.393	0.415	0.393	0.415	0.552	0.552	0.581	0.552	0.581	0.644	0.644	0.684	0.644	0.684	ns
HSLVDCI_15_S	0.393	0.393	0.415	0.393	0.415	0.748	0.748	0.802	0.748	0.802	0.827	0.827	0.890	0.827	0.890	ns
HSLVDCI_18_F	0.424	0.424	0.447	0.424	0.447	0.445	0.445	0.461	0.445	0.461	0.566	0.566	0.595	0.566	0.595	ns
HSLVDCI_18_M	0.424	0.424	0.447	0.424	0.447	0.567	0.567	0.598	0.567	0.598	0.658	0.658	0.699	0.658	0.699	ns
HSLVDCI_18_S	0.424	0.424	0.447	0.424	0.447	0.761	0.761	0.817	0.761	0.817	0.836	0.836	0.900	0.836	0.900	ns
HSTL_I_12_F	0.378	0.378	0.399	0.378	0.399	0.423	0.423	0.443	0.423	0.443	0.553	0.553	0.582	0.553	0.582	ns
HSTL_I_12_M	0.378	0.378	0.399	0.378	0.399	0.551	0.551	0.582	0.551	0.582	0.642	0.642	0.679	0.642	0.679	ns
HSTL_I_12_S	0.378	0.378	0.399	0.378	0.399	0.750	0.750	0.799	0.750	0.799	0.813	0.813	0.868	0.813	0.868	ns
HSTL_I_18_F	0.322	0.322	0.339	0.322	0.339	0.456	0.456	0.474	0.456	0.474	0.576	0.576	0.606	0.576	0.606	ns
HSTL_I_18_M	0.322	0.322	0.339	0.322	0.339	0.569	0.569	0.602	0.569	0.602	0.653	0.653	0.692	0.653	0.692	ns
HSTL_I_18_S	0.322	0.322	0.339	0.322	0.339	0.781	0.781	0.833	0.781	0.833	0.816	0.816	0.871	0.816	0.871	ns
HSTL_I_DCI_12_F	0.378	0.378	0.399	0.378	0.399	0.406	0.406	0.429	0.406	0.429	0.534	0.534	0.564	0.534	0.564	ns
HSTL_I_DCI_12_M	0.378	0.378	0.399	0.378	0.399	0.556	0.556	0.586	0.556	0.586	0.654	0.654	0.694	0.654	0.694	ns
HSTL_I_DCI_12_S	0.378	0.378	0.399	0.378	0.399	0.754	0.754	0.803	0.754	0.803	0.842	0.842	0.907	0.842	0.907	ns
HSTL_I_DCI_18_F	0.321	0.321	0.339	0.321	0.339	0.445	0.445	0.461	0.445	0.461	0.566	0.566	0.595	0.566	0.595	ns
HSTL_I_DCI_18_M	0.321	0.321	0.339	0.321	0.339	0.554	0.554	0.585	0.554	0.585	0.643	0.643	0.684	0.643	0.684	ns
HSTL_I_DCI_18_S	0.321	0.321	0.339	0.321	0.339	0.761	0.761	0.817	0.761	0.817	0.836	0.836	0.900	0.836	0.900	ns
HSTL_I_DCI_F	0.393	0.393	0.415	0.393	0.415	0.431	0.431	0.445	0.431	0.445	0.555	0.555	0.575	0.555	0.575	ns
HSTL_I_DCI_M	0.393	0.393	0.415	0.393	0.415	0.552	0.552	0.581	0.552	0.581	0.644	0.644	0.684	0.644	0.684	ns

Table 78: **Input Delay Measurement Methodology *(Cont'd)***

Description	I/O Standard Attribute	V_L [1][2]	V_H [1][2]	V_{MEAS} [1][4][6]	V_{REF} [1][3][5]
SUB_LVDS, 1.8V	SUB_LVDS	0.9 – 0.125	0.9 + 0.125	0[6]	–
SLVS, 1.8V	SLVS_400_18	0.9 – 0.125	0.9 + 0.125	0[6]	–
SLVS, 2.5V	SLVS_400_25	1.25 – 0.125	1.25 + 0.125	0[6]	–
LVPECL, 2.5V	LVPECL	1.25 – 0.125	1.25 + 0.125	0[6]	–
MIPI D-PHY (high speed) 1.2V	MIPI_DPHY_DCI_HS	0.2 – 0.125	0.2 + 0.125	0[6]	–
MIPI D-PHY (low power) 1.2V	MIPI_DPHY_DCI_LP	0.715 – 0.2	0.715 + 0.2	0[6]	–

Notes:

1. The input delay measurement methodology parameters for LVDCI/HSLVDCI are the same for LVCMOS standards of the same voltage. Parameters for all other DCI standards are the same for the corresponding non-DCI standards.
2. Input waveform switches between V_L and V_H.
3. Measurements are made at typical, minimum, and maximum V_{REF} values. Reported delays reflect worst case of these measurements. V_{REF} values listed are typical.
4. Input voltage level from which measurement starts.
5. This is an input voltage reference that bears no relation to the V_{REF}/V_{MEAS} parameters found in IBIS models and/or noted in Figure 1.
6. The value given is the differential input voltage.

Table 102: **GTH Transceiver User Clock Switching Characteristics(1) *(Cont'd)***

Symbol	Description	Data Width Conditions (Bit)		Speed Grade and V_{CCINT} Operating Voltages					Units
				0.90V	0.85V		0.72V		
		Internal Logic	Interconnect Logic	-3(2)	-2(2)(3)	-1(4)(5)	-2(3)	-1(5)	
$F_{TXOUTPROGDIV}$	TXOUTCLK maximum frequency sourced from TXPROGDIVCLK			511.719	511.719	511.719	511.719	511.719	MHz
$F_{RXOUTPROGDIV}$	RXOUTCLK maximum frequency sourced from RXPROGDIVCLK			511.719	511.719	511.719	511.719	511.719	MHz
F_{TXIN}	TXUSRCLK(6) maximum frequency	16	16, 32	511.719	511.719	390.625	390.625	322.266	MHz
		32	32, 64	511.719	511.719	390.625	390.625	322.266	MHz
		20	20, 40	409.375	409.375	312.500	312.500	257.813	MHz
		40	40, 80	409.375	409.375	312.500	312.500	257.813	MHz
F_{RXIN}	RXUSRCLK(6) maximum frequency	16	16, 32	511.719	511.719	390.625	390.625	322.266	MHz
		32	32, 64	511.719	511.719	390.625	390.625	322.266	MHz
		20	20, 40	409.375	409.375	312.500	312.500	257.813	MHz
		40	40, 80	409.375	409.375	312.500	312.500	257.813	MHz
F_{TXIN2}	TXUSRCLK2(6) maximum frequency	16	16	511.719	511.719	390.625	390.625	322.266	MHz
		16	32	255.859	255.859	195.313	195.313	161.133	MHz
		32	32	511.719	511.719	390.625	390.625	322.266	MHz
		32	64	255.859	255.859	195.313	195.313	161.133	MHz
		20	20	409.375	409.375	312.500	312.500	257.813	MHz
		20	40	204.688	204.688	156.250	156.250	128.906	MHz
		40	40	409.375	409.375	312.500	312.500	257.813	MHz
		40	80	204.688	204.688	156.250	156.250	128.906	MHz
F_{RXIN2}	RXUSRCLK2(6) maximum frequency	16	16	511.719	511.719	390.625	390.625	322.266	MHz
		16	32	255.859	255.859	195.313	195.313	161.133	MHz
		32	32	511.719	511.719	390.625	390.625	322.266	MHz
		32	64	255.859	255.859	195.313	195.313	161.133	MHz
		20	20	409.375	409.375	312.500	312.500	257.813	MHz
		20	40	204.688	204.688	156.250	156.250	128.906	MHz
		40	40	409.375	409.375	312.500	312.500	257.813	MHz
		40	80	204.688	204.688	156.250	156.250	128.906	MHz

Notes:

1. Clocking must be implemented as described in *UltraScale Architecture GTH Transceiver User Guide* (UG576).
2. For speed grades -3E, -2E, and -2I, a 16-bit and 20-bit internal data path can only be used for line rates less than 8.1875 Gb/s.
3. For speed grade -2LE, a 16-bit and 20-bit internal data path can only be used for line rates less than 8.1875 Gb/s when V_{CCINT} = 0.85V or 6.25 Gb/s when V_{CCINT} = 0.72V.
4. For speed grades -1E and -1I, a 16-bit and 20-bit internal data path can only be used for line rates less than 6.25 Gb/s.
5. For speed grade -1LI, a 16-bit and 20-bit internal data path can only be used for line rates less than 6.25 Gb/s when V_{CCINT} = 0.85V or 5.15625 Gb/s when V_{CCINT} = 0.72V.
6. When the gearbox is used, these maximums refer to the XCLK. For more information, see the *Valid Data Width Combinations for TX Asynchronous Gearbox* table in the *UltraScale Architecture GTH Transceiver User Guide* (UG576).

Table 103: **GTH Transceiver Transmitter Switching Characteristics**

Symbol	Description	Condition	Min	Typ	Max	Units
F_{GTHTX}	Serial data rate range		0.500	–	F_{GTHMAX}	Gb/s
T_{RTX}	TX rise time	20%–80%	–	21	–	ps
T_{FTX}	TX fall time	80%–20%	–	21	–	ps
T_{LLSKEW}	TX lane-to-lane skew(1)		–	–	500.00	ps
$T_{J16.375}$	Total jitter(2)(4)	16.375 Gb/s	–	–	0.28	UI
$D_{J16.375}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J15.0}$	Total jitter(2)(4)	15.0 Gb/s	–	–	0.28	UI
$D_{J15.0}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J14.1}$	Total jitter(2)(4)	14.1 Gb/s	–	–	0.28	UI
$D_{J14.1}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J14.1}$	Total jitter(2)(4)	14.025 Gb/s	–	–	0.28	UI
$D_{J14.1}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J13.1}$	Total jitter(2)(4)	13.1 Gb/s	–	–	0.28	UI
$D_{J13.1}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J12.5\_QPLL}$	Total jitter(2)(4)	12.5 Gb/s	–	–	0.28	UI
$D_{J12.5\_QPLL}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J12.5\_CPLL}$	Total jitter(3)(4)	12.5 Gb/s	–	–	0.33	UI
$D_{J12.5\_CPLL}$	Deterministic jitter(3)(4)		–	–	0.17	UI
$T_{J11.3\_QPLL}$	Total jitter(2)(4)	11.3 Gb/s	–	–	0.28	UI
$D_{J11.3\_QPLL}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J10.3125\_QPLL}$	Total jitter(2)(4)	10.3125 Gb/s	–	–	0.28	UI
$D_{J10.3125\_QPLL}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J10.3125\_CPLL}$	Total jitter(3)(4)	10.3125 Gb/s	–	–	0.33	UI
$D_{J10.3125\_CPLL}$	Deterministic jitter(3)(4)		–	–	0.17	UI
$T_{J9.953\_QPLL}$	Total jitter(2)(4)	9.953 Gb/s	–	–	0.28	UI
$D_{J9.953\_QPLL}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J9.953\_CPLL}$	Total jitter(3)(4)	9.953 Gb/s	–	–	0.33	UI
$D_{J9.953\_CPLL}$	Deterministic jitter(3)(4)		–	–	0.17	UI
$T_{J8.0}$	Total jitter(3)(4)	8.0 Gb/s	–	–	0.32	UI
$D_{J8.0}$	Deterministic jitter(3)(4)		–	–	0.17	UI
$T_{J6.6}$	Total jitter(3)(4)	6.6 Gb/s	–	–	0.30	UI
$D_{J6.6}$	Deterministic jitter(3)(4)		–	–	0.15	UI
$T_{J5.0}$	Total jitter(3)(4)	5.0 Gb/s	–	–	0.30	UI
$D_{J5.0}$	Deterministic jitter(3)(4)		–	–	0.15	UI
$T_{J4.25}$	Total jitter(3)(4)	4.25 Gb/s	–	–	0.30	UI
$D_{J4.25}$	Deterministic jitter(3)(4)		–	–	0.15	UI
$T_{J4.0}$	Total jitter(3)(4)	4.0 Gb/s	–	–	0.32	UI
$D_{J4.0}$	Deterministic jitter(3)(4)		–	–	0.16	UI
$T_{J3.20}$	Total jitter(3)(4)	3.20 Gb/s(5)	–	–	0.20	UI
$D_{J3.20}$	Deterministic jitter(3)(4)		–	–	0.10	UI

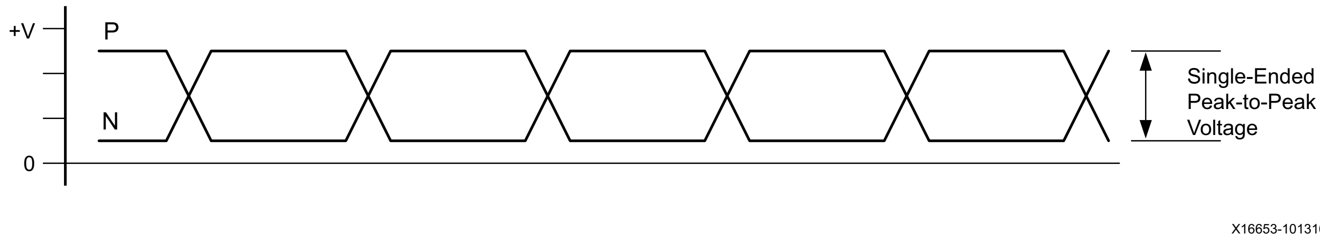

Figure 5: **Single-Ended Peak-to-Peak Voltage**

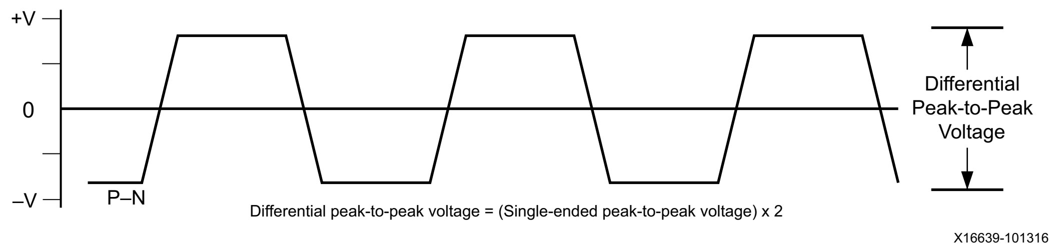

Figure 6: **Differential Peak-to-Peak Voltage**

Table 107 and Table 108 summarize the DC specifications of the clock input of the GTY transceivers in Zynq UltraScale+ MPSoCs. Consult the *UltraScale Architecture GTY Transceiver User Guide* (UG578) for further details.

Table 107: **GTY Transceiver Clock DC Input Level Specification**

Symbol	DC Parameter	Min	Typ	Max	Units
V_{IDIFF}	Differential peak-to-peak input voltage	250	–	2000	mV
R_{IN}	Differential input resistance	–	100	–	Ω
C_{EXT}	Required external AC coupling capacitor	–	10	–	nF

Table 108: **GTY Transceiver Clock Output Level Specification**

Symbol	Description	Conditions	Min	Typ	Max	Units
V_{OL}	Output Low voltage for P and N	R_T = 100Ω across P and N signals	100	–	330	mV
V_{OH}	Output High voltage for P and N	R_T = 100Ω across P and N signals	500	–	700	mV
V_{DDOUT}	Differential output voltage (P–N), P = High (N–P), N = High	R_T = 100Ω across P and N signals	300	–	430	mV
V_{CMOUT}	Common mode voltage	R_T = 100Ω across P and N signals	300	–	500	mV

GTY Transceiver Electrical Compliance

The *UltraScale Architecture GTY Transceiver User Guide* (UG578) contains recommended use modes that ensure compliance for the protocols listed in Table 117. The transceiver wizard provides the recommended settings for those use cases and for protocol specific characteristics.

Table 117: **GTY Transceiver Protocol List**

Protocol	Specification	Serial Rate (Gb/s)	Electrical Compliance
CAUI-4	IEEE 802.3-2012	25.78125	Compliant
28 Gb/s backplane	CEI-25G-LR	25–28.05	Compliant
Interlaken	OIF-CEI-6G, OIF-CEI-11GSR, OIF-CEI-28G-MR	4.25–25.78125	Compliant
100GBASE-KR4	IEEE 802.3bj-2014, CEI-25G-LR	25.78125	Compliant(1)
100GBASE-CR4	IEEE 802.3bj-2014, CEI-25G-LR	25.78125	Compliant(1)
50GBASE-KR4	IEEE 802.3by-2014, CEI-25G-LR	25.78125	Compliant(1)
50GBASE-CR4	IEEE 802.3by-2014, CEI-25G-LR	25.78125	Compliant(1)
25GBASE-KR4	IEEE 802.3by-2014, CEI-25G-LR	25.78125	Compliant(1)
25GBASE-CR4	IEEE 802.3by-2014, CEI-25G-LR	25.78125	Compliant(1)
OTU4 (OTL4.4) CFP2	OIF-CEI-28G-VSR	27.952493–32.75	Compliant
OTU4 (OTL4.4) CFP	OIF-CEI-11G-MR	11.18–13.1	Compliant
CAUI-10	IEEE 802.3-2012	10.3125	Compliant
nPPI	IEEE 802.3-2012	10.3125	Compliant
10GBASE-KR(2)	IEEE 802.3-2012	10.3125	Compliant
SFP+	SFF-8431 (SR and LR)	9.95328–11.10	Compliant
XFP	INF-8077i, revision 4.5	10.3125	Compliant
RXAUI	CEI-6G-SR	6.25	Compliant
XAUI	IEEE 802.3-2012	3.125	Compliant
1000BASE-X	IEEE 802.3-2012	1.25	Compliant
5.0G Ethernet	IEEE 802.3bx (PAR)	5	Compliant
2.5G Ethernet	IEEE 802.3bx (PAR)	2.5	Compliant
HiGig, HiGig+, HiGig2	IEEE 802.3-2012	3.74, 6.6	Compliant
QSGMII	QSGMII v1.2 (Cisco System, ENG-46158)	5	Compliant
OTU2	ITU G.8251	10.709225	Compliant
OTU4 (OTL4.10)	OIF-CEI-11G-SR	11.180997	Compliant
OC-3/12/48/192	GR-253-CORE	0.1555–9.956	Compliant
PCIe Gen1, 2, 3	PCI Express base 3.0	2.5, 5.0, and 8.0	Compliant
SDI(3)	SMPTE 424M-2006	0.27–2.97	Compliant
UHD-SDI(3)	SMPTE ST-2081 6G, SMPTE ST-2082 12G	6 and 12	Compliant
Hybrid memory cube (HMC)	HMC-15G-SR	10, 12.5, and 15.0	Compliant
MoSys bandwidth engine	CEI-11-SR and CEI-11-SR (overclocked)	10.3125, 15.5	Compliant
CPRI	CPRI_v_6_1_2014-07-01	0.6144–12.165	Compliant
Passive optical network (PON)	10G-EPON, 1G-EPON, NG-PON2, XG-PON, and 2.5G-PON	0.155–10.3125	Compliant
JESD204a/b	OIF-CEI-6G, OIF-CEI-11G	3.125–12.5	Compliant

Table 117: **GTY Transceiver Protocol List *(Cont'd)***

Protocol	Specification	Serial Rate (Gb/s)	Electrical Compliance
Serial RapidIO	RapidIO specification 3.1	1.25–10.3125	Compliant
DisplayPort	DP 1.2B CTS	1.62–5.4	Compliant(3)
Fibre channel	FC-PI-4	1.0625–14.025	Compliant
SATA Gen1, 2, 3	Serial ATA revision 3.0 specification	1.5, 3.0, and 6.0	Compliant
SAS Gen1, 2, 3	T10/BSR INCITS 519	3.0, 6.0, and 12.0	Compliant
SFI-5	OIF-SFI5-01.0	0.625 - 12.5	Compliant
Aurora	CEI-6G, CEI-11G-LR	All rates	Compliant

Notes:

1. 25 dB loss at Nyquist without FEC.
2. The transition time of the transmitter is faster than the IEEE Std 802.3-2012 specification.
3. This protocol requires external circuitry to achieve compliance.

Integrated Interface Block for Interlaken

More information and documentation on solutions using the integrated interface block for Interlaken can be found at UltraScale+ Interlaken. The *UltraScale Architecture and Product Overview* (DS890) lists how many blocks are in each Zynq UltraScale+ MPSoC. This section describes the following Interlaken configurations.

- 12 x 12.5 Gb/s protocol and lane logic mode (Table 118).
- 6 x 25.78125 Gb/s and 6 x 28.21 Gb/s protocol and lane logic mode (Table 119).
- 12 x 25.78125 Gb/s lane logic only mode (Table 120).

Zynq UltraScale+ MPSoCs in the SFVB784, FFVA676, and FFVA1156 packages are only supported using the 12 x 12.5 Gb/s Interlaken configuration. See Table 109 for the F_{GTYMAX} description.

Table 118: **Maximum Performance for Interlaken 12 x 12.5 Gb/s Protocol and Lane Logic Mode Designs**

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages										Units
		0.90V		0.85V				0.72V				
		-3		-2		-1		-2		-1		
$F_{RX\_SERDES\_CLK}$	Receive serializer/deserializer clock	195.32		195.32		195.32		195.32		195.32		MHz
$F_{TX\_SERDES\_CLK}$	Transmit serializer/deserializer clock	195.32		195.32		195.32		195.32		195.32		MHz
F_{DRP_CLK}	Dynamic reconfiguration port clock	250.00		250.00		250.00		250.00		250.00		MHz
		Min(1)	Max	Min(1)	Max	Min(1)	Max	Min(1)	Max	Min(1)	Max	
F_{CORE_CLK}	Interlaken core clock	300.00	322.27	300.00	322.27	300.00	322.27	300.00	322.27	300.00	322.27	MHz
F_{LBUS_CLK}	Interlaken local bus clock	300.00	322.27	300.00	322.27	300.00	322.27	300.00	322.27	300.00	322.27	MHz

Notes:

1. These are the minimum clock frequencies at the maximum lane performance.

Video Codec Performance

The *UltraScale Architecture and Product Overview* (DS890) lists the Zynq UltraScale+ MPSoC EV devices that include the Video Codec unit (VCU).

Table 123: **VCU Performance**

Description	Speed Grade and V_{CCINT} Operating Voltages					Units
	0.90V	0.85V		0.72V		
	-3	-2	-1	-2	-1	
Video Codec decoder block maximum frequency (H.264/5 10-bit 4:2:2)	667	667	667	667	667	MHz

PL System Monitor Specifications

Table 124: **PL SYSMON Specifications**

Parameter	Symbol	Comments/Conditions	Min	Typ	Max	Units
V_{CCADC} = 1.8V ±3%, V_{REFP} = 1.25V, V_{REFN} = 0V, ADCCLK = 5.2 MHz, T_j = –40°C to 100°C, typical values at T_j = 40°C						
ADC Accuracy[(1)]						
Resolution			10	–	–	Bits
Integral nonlinearity[(2)]	INL		–	–	±1.5	LSBs
Differential nonlinearity	DNL	No missing codes, guaranteed monotonic	–	–	±1	LSBs
Offset error		Offset calibration enabled	–	–	±2	LSBs
Gain error			–	–	±0.4	%
Sample rate			–	–	0.2	MS/s
RMS code noise		External 1.25V reference	–	–	1	LSBs
		On-chip reference	–	1	–	LSBs
ADC Accuracy at Extended Temperatures						
Resolution		T_j = –55°C to 125°C	10	–	–	Bits
Integral nonlinearity[(2)]	INL	T_j = –55°C to 125°C	–	–	±1.5	LSBs
Differential nonlinearity	DNL	No missing codes, guaranteed monotonic (T_j = –55°C to 125°C)	–	–	±1	LSBs
Analog Inputs[(2)]						
ADC input ranges		Unipolar operation	0	–	1	V
		Bipolar operation	–0.5	–	+0.5	V
		Unipolar common mode range (FS input)	0	–	+0.5	V
		Bipolar common mode range (FS input)	+0.5	–	+0.6	V
Maximum external channel input ranges		Adjacent channels set within these ranges should not corrupt measurements on adjacent channels	–0.1	–	V_{CCADC}	V